



BC 171 • BC 172 • BC 173

NPN HIGH GAIN LOW NOISE SILICON PLANAR EPITAXIAL TRANSISTOR

BC 171
BC 172
BC 173

FEATURES

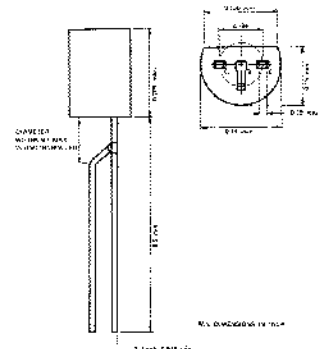
- High Breakdown Voltage $V_{CE0} \dots 50V$ (BC171)
- Available in Different Current Gain Groupings
- Low Noise N.F. $\dots 4dB_{max}$ @ $0.2mA$ (BC173)

APPLICATIONS

- Audio Amplifier Driver Stage
- Television Receiver Circuits
- Low Power General Purpose
- Low Noise Pre-Amplifier (BC173)

MECHANICAL OUTLINE

μ -135
(Lead Code A)
(TO-92 Variant)



THERMAL CHARACTERISTICS

Thermal Resistance from Junction to Ambient $\theta(j-amb)$
Maximum Collector Junction Temperature
Storage Temperature Range
Soldering Temperature (10 sec. time limit)

$0.42^{\circ}C/mW$
 $150^{\circ}C$
 $-65^{\circ}C$ to $150^{\circ}C$
 $260^{\circ}C$

ABSOLUTE MAXIMUM RATINGS

Continuous Power Dissipation @ $25^{\circ}C$ Ambient
Continuous Collector Current
Collector-Base Voltage
Collector-Emmitter Voltage
Base-Emmitter Voltage

	BC 171	BC 172	BC 173
Continuous Power Dissipation	300 mW	300 mW	300 mW
Continuous Collector Current	100 mA	100 mA	100 mA
Collector-Base Voltage	50 V	25 V	25 V
Collector-Emmitter Voltage	45 V	25 V	25 V
Base-Emmitter Voltage	6 V	5 V	5 V

ELECTRICAL CHARACTERISTICS @ $25^{\circ}C$ free air temperature:

PARAMETER	SYMBOL	BC 171		BC 172		BC 173		UNIT	TEST CONDITIONS
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Collector-Base Cutoff Current	I_{CBO}		15					nA	$V_{CB} = 45V$
Collector-Base Cutoff Current	I_{CBO}				15		15	nA	$V_{CB} = 20V$
Collector-Emmitter Saturation Voltage	$V_{CE(sat)}$		0.25	0.25	0.25	0.25	0.25	V	$I_C = 10mA$ $I_B = 0.5mA$
Collector-Emmitter Saturation Voltage	$V_{CE(sat)}$		0.6	0.6	0.6	0.6	0.6	V	$I_C = 100mA$ $I_B = 5mA$
Base-Emmitter On Voltage	$V_{BE(sat)}$	0.55	0.7	0.55	0.7	0.55	0.7	V	$V_{CE} = 5V$ $I_C = 2mA$
Forward Current Transfer Ratio	h_{FE}	110	450	110	800	110	800		$V_{CE} = 5V$ $I_C = 2mA$
Small Signal Current Gain	h_{fe}	1.5		1.5		1.5			$f = 100MHz$ $I_C = 10mA$ $V_{CE} = 5V$
Collector Output Capacitance	C_{ob}		6		6		6	pF	$V_{CE} = 10V$ $f = 1MHz$ $I_C = 0$
Noise Figure (Narrow Band)	N.F.		10		10		4	dB	$V_{CE} = 5V$ $I_C = 0.2mA$ $R_g = 2K\Omega$ $f = 1KC$ $BW = 200Hz$
Noise Figure (Wide Band)	N.F.						4	dB	$V_{CE} = 5V$ $I_C = 0.2mA$ $R_g = 2K\Omega$ $f = 30Hz$ to $15KHz$

* D. C. CURRENT GAIN GROUPINGS

TYPE	BC 171A		BC 172B BC 173B		BC 172C BC 173C		BC 171A BC 172A BC 173A		BC 171B BC 172B BC 173B		BC 172C BC 173C	
	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.
$V_{CB} = 5V$ $I_C = 0.01mA$		40		40		100						
$V_{CE} = 5V$ $I_C = 2mA$							110	220	200	450	420	800

TYPICAL TWO PORT CHARACTERISTICS (h parameters)

TYPE	BC 171A BC 172A BC 173A	BC 171B BC 172B BC 173B	BC 172C BC 173C	UNIT	TEST CONDITIONS
PARAMETERS					$V_{CE} = 5V$ $I_C = 2mA$ $f = 1KHz$
h_{fe}	180	300	600		
h_{ie}	2.5	4	8	Kohm	
h_{re}	3×10^{-4}	6×10^{-4}	8×10^{-4}		
h_{oe}	20	26	50	μS	

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NPN SILICON PLANAR EPITAXIAL TRANSISTOR

TYPICAL ELECTRICAL CHARACTERISTICS BC 171 • BC 172 • BC 173

